



SANYO Semiconductors

DATA SHEET

3LP04MH — P-Channel Silicon MOSFET

General-Purpose Switching Device Applications

Features

- 1.5V drive.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		-30	V
Gate-to-Source Voltage	V _{GSS}		±10	V
Drain Current (DC)	I _D		-200	mA
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	-800	mA
Allowable Power Dissipation	P _D	Mounted on a ceramic board (900mm²×0.8mm)	0.6	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR) _{DSS}	I _D =-1mA, V _{GS} =0V	-30			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V, V _{GS} =0V			-1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±8V, V _{DS} =0V			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =-10V, I _D =-100μA	-0.4		-1.4	V
Forward Transfer Admittance	y _{fs}	V _{DS} =-10V, I _D =-100mA	190	320		mS
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =-100mA, V _{GS} =-4V		1.8	2.4	Ω
	R _{DS(on)2}	I _D =-50mA, V _{GS} =-2.5V		2.4	3.4	Ω
	R _{DS(on)3}	I _D =-10mA, V _{GS} =-1.5V		4.5	9.0	Ω
Input Capacitance	C _{iss}	V _{DS} =-10V, f=1MHz		35		pF
Output Capacitance	C _{oss}	V _{DS} =-10V, f=1MHz		7.2		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} =-10V, f=1MHz		2.1		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		75		ns
Rise Time	t _r	See specified Test Circuit.		170		ns
Turn-OFF Delay Time	t _{d(off)}	See specified Test Circuit.		550		ns
Fall Time	t _f	See specified Test Circuit.		350		ns

Marking : QD

Continued on next page.

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3LP04MH

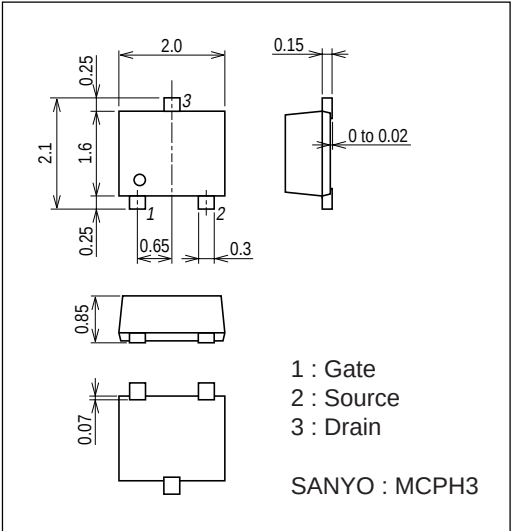
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Total Gate Charge	Qg	V _{DS} =-10V, V _{GS} =-4V, I _D =-200mA		0.58		nC
Gate-to-Source Charge	Qgs	V _{DS} =-10V, V _{GS} =-4V, I _D =-200mA		0.17		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =-10V, V _{GS} =-4V, I _D =-200mA		0.12		nC
Diode Forward Voltage	V _{SD}	I _S =-200mA, V _{GS} =0V		-0.89	-1.2	V

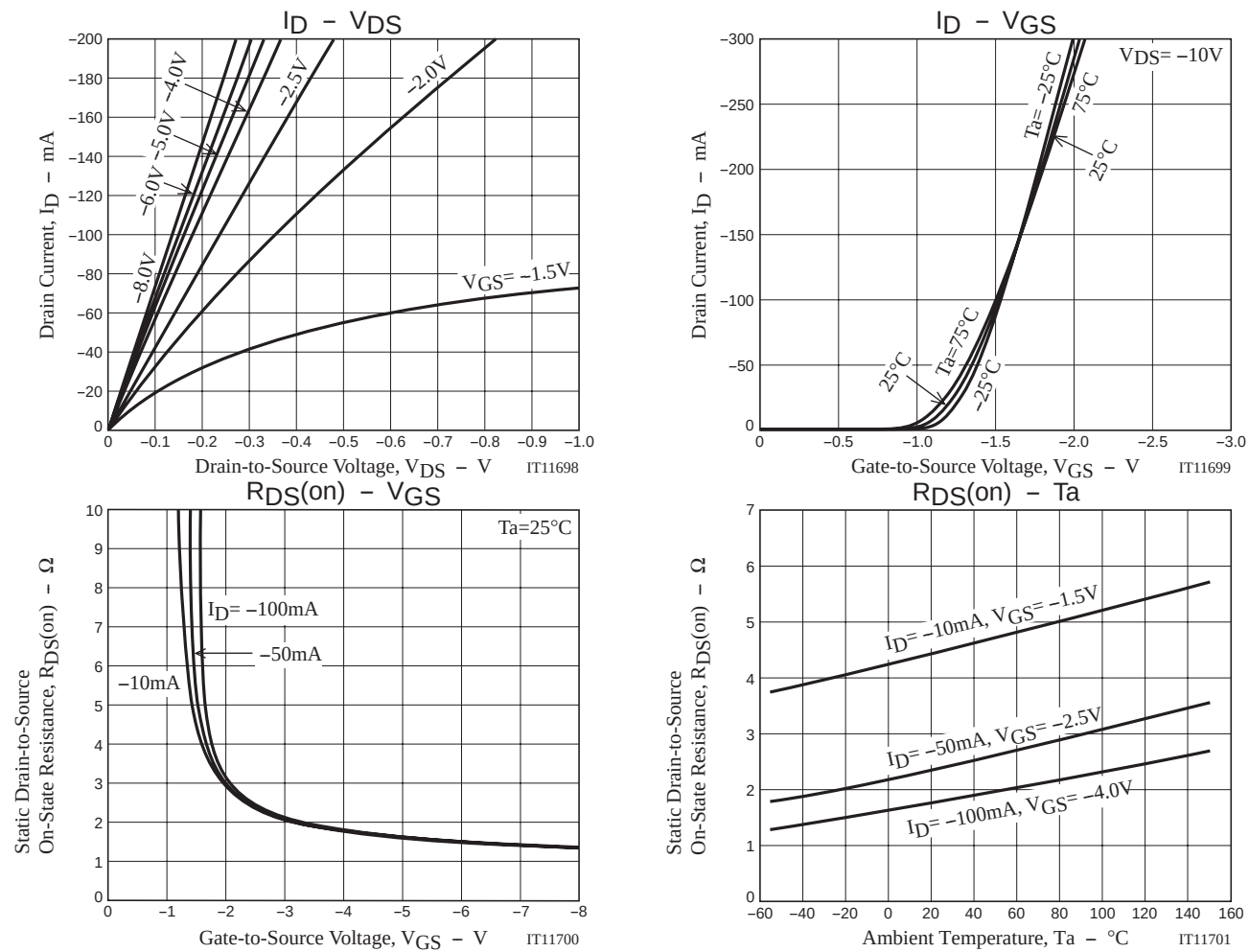
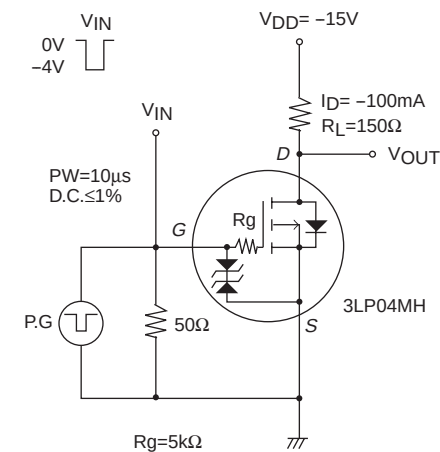
Package Dimensions

unit : mm (typ)

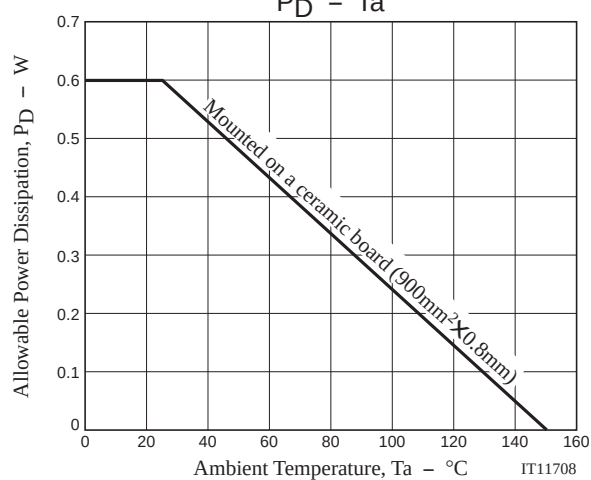
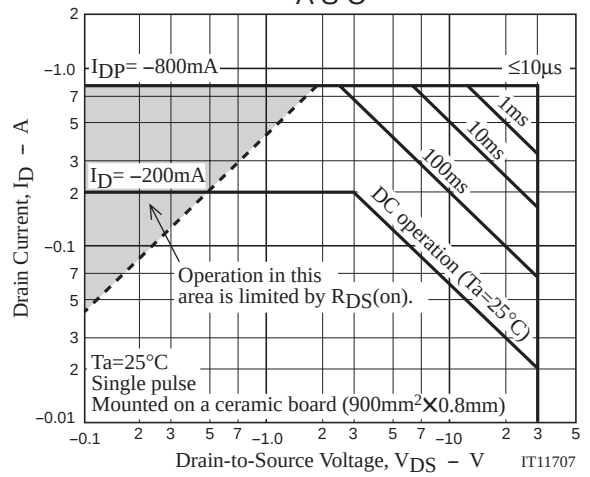
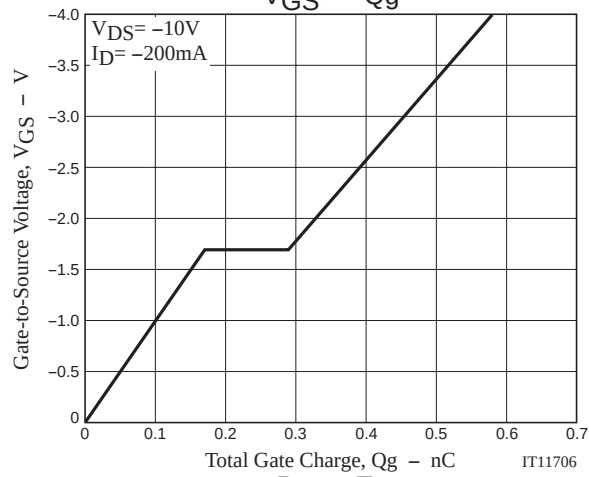
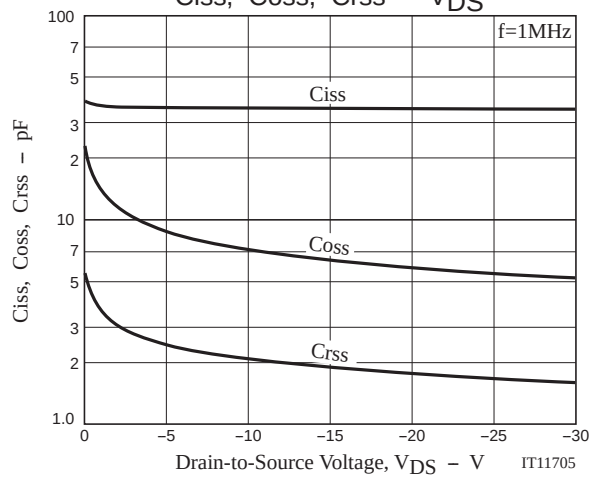
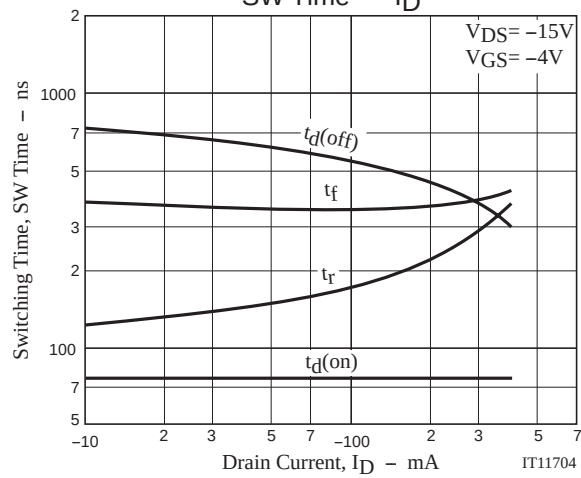
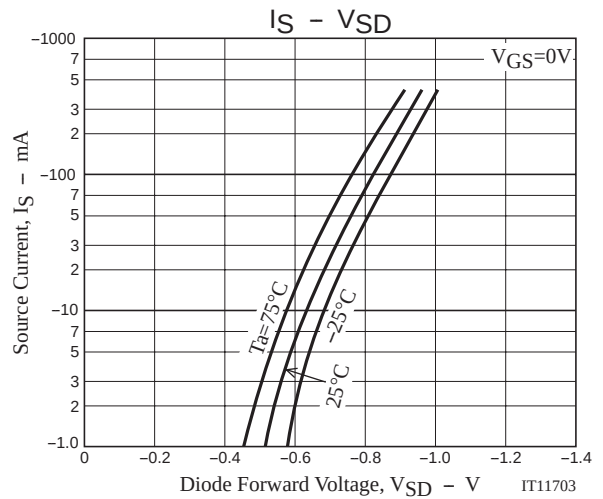
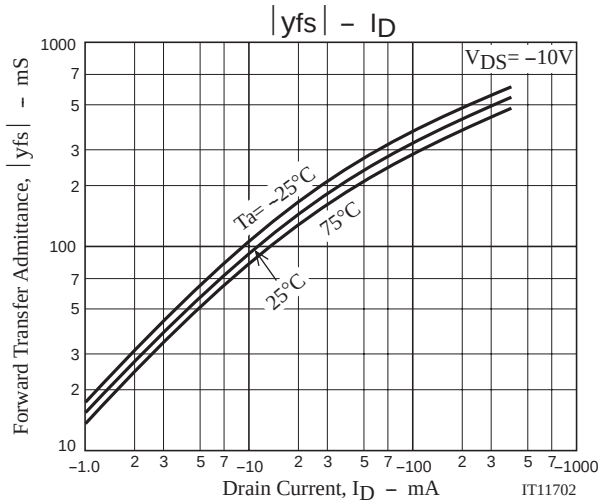
7019A-003



Switching Time Test Circuit



3LP04MH



Note on usage : Since the 3LP04MH is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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